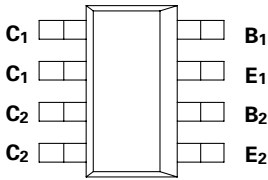


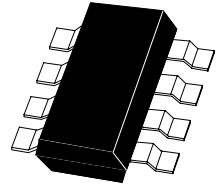
# SM-8 DUAL NPN MEDIUM POWER HIGH GAIN TRANSISTORS

ISSUE 1 - NOVEMBER 1995

## ZDT694



PARTMARKING DETAIL - T694



SM-8  
(8 LEAD SOT223)

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CB0}$	120	V
Collector-Emitter Voltage	$V_{CE0}$	120	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Peak Pulse Current	$I_{CM}$	1	A
Continuous Collector Current	$I_C$	0.5	A
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	°C

### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^\circ\text{C}^*$ Any single die "on" Both die "on" equally	$P_{tot}$	2.25 2.75	W W
Derate above $25^\circ\text{C}^*$ Any single die "on" Both die "on" equally		18 22	mW/°C mW/°C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6 45.5	°C/W °C/W

\* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

# ZDT694

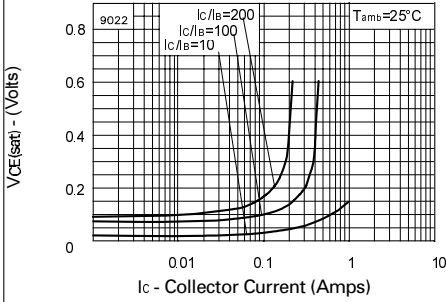
## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ ).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	120			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cutoff Current	$I_{CBO}$			0.1	$\mu\text{A}$	$V_{CB}=100\text{V}$
Emitter Cutoff Current	$I_{EBO}$			0.1	$\mu\text{A}$	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.25 0.5	V V	$I_C=0.1\text{A}, I_B=0.5\text{mA}^*$ $I_C=0.4\text{A}, I_B=5\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	$I_C=1\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	500 400 150				$I_C=100\text{mA}, V_{CE}=2\text{V}^*$ $I_C=200\text{mA}, V_{CE}=2\text{V}^*$ $I_C=400\text{mA}, V_{CE}=2\text{V}^*$
Transition Frequency	$f_T$	130			MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	$C_{ibo}$		200		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Output Capacitance	$C_{obo}$		9		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	$t_{on}$ $t_{off}$		80 2900		ns ns	$I_C=100\text{mA}, I_{B1}=10\text{mA}$ $I_{B2}=10\text{mA}, V_{CC}=50\text{V}$

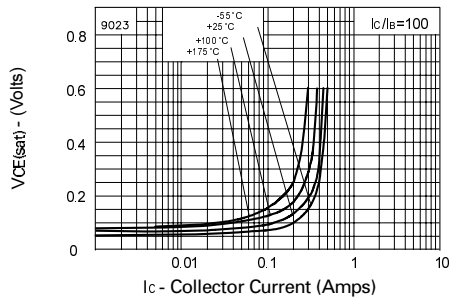
\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

# ZDT694

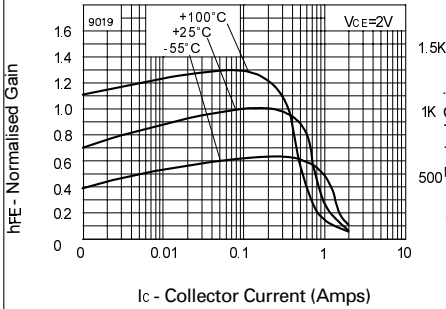
## TYPICAL CHARACTERISTICS



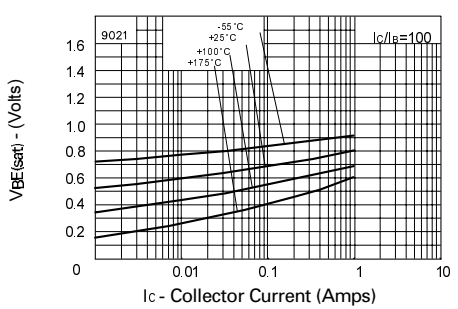
**VCE(sat) v IC**



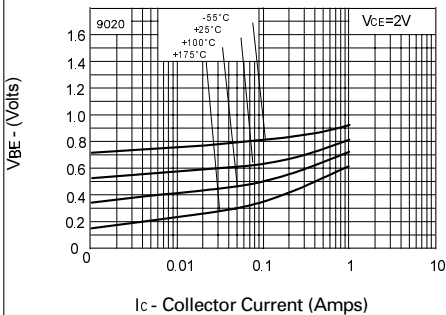
**VCE(sat) v IC**



**hFE v IC**



**VBE(sat) v IC**



**VBE(on) v IC**